

TC74AC563, 573 Octal D-Type Latch with 3-State Output

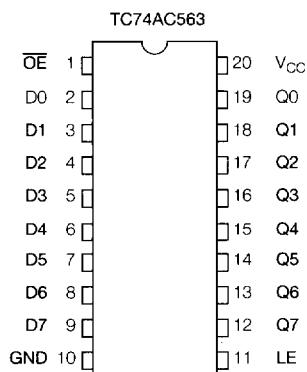
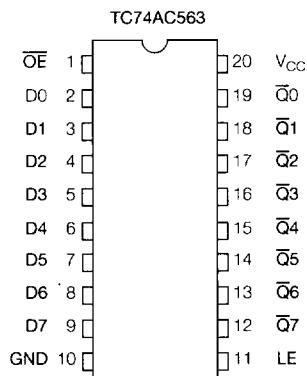
563: Inverting

573: Non-Inverting

Features:

- High Speed:** $t_{\text{pd}} = 6.0\text{ns}$ (typ.) at $V_{\text{CC}} = 5\text{V}$
- Low Power Dissipation:** $I_{\text{CC}} = 8\mu\text{A}$ (max.) at $T_a = 25^\circ\text{C}$
- High Noise Immunity:** $V_{\text{NIH}} = V_{\text{NIL}} = 28\% V_{\text{CC}}$ (min.)
- Symmetrical Output Impedance:** $I_{\text{OH}} = I_{\text{OL}} = 24\text{mA}$ (min.). Capability of driving 50Ω transmission lines.
- Balanced Propagation Delays:** $t_{\text{pLH}} = t_{\text{pHL}}$
- Wide Operating Voltage Range:** V_{CC} (opr) = $2\text{V} \sim 5.5\text{V}$
- Pin and Function Compatible with 74F563/573**
- AC563 Available in DIP, SOIC and SOP Packages**
- AC573 Available in DIP, SOIC, SOP, and SSOP Packages**

Pin Assignment



The TC74AC563 and TC74AC573 are advanced high speed CMOS OCTAL LATCHES with 3-STATE OUTPUTS fabricated with silicon gate and double-layer metal wiring C²MOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL, while maintaining the CMOS low power dissipation.

These 8-bit D-type latches are controlled by a latch enable input (LE) and a output enable input ($\overline{\text{OE}}$).

When the $\overline{\text{OE}}$ input is high, the eight outputs are in a high impedance state.

The TC74AC540 is an inverting type, and the TC74AC541 is a non-inverting type.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

Truth Table

INPUTS			OUTPUTS	
$\overline{\text{OE}}$	LE	D	Q(573)	$\overline{Q}(563)$
H	X	X	Z	Z
L	L	X	Q_n	\overline{Q}_n
L	H	L	L	H
L	H	H	H	L

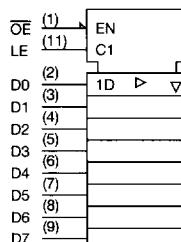
X: Don't Care

Z: High Impedance

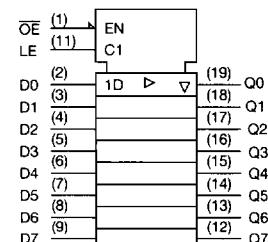
Q_n (\overline{Q}_n): Q (Q̄) outputs are latched at the time when the LE input is taken to a low logic level.

IEC Logic Symbol

TC74AC563



TC74AC573



Absolute Maximum Ratings

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~ V_{CC} + 0.5	V
DC Output Voltage	V_{OUT}	-0.5~ V_{CC} + 0.5	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 50	mA
DC Output Current	I_{OUT}	± 50	mA
DC V_{CC} /Ground Current	I_{CC}	± 200	mA
Power Dissipation	P_D	500 (DIP) /180 (SOP)	mW
Storage Temperature	T_{STG}	-65~150	°C
Lead Temperature 10sec	T_L	300	°C

* 500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$.
From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of
 $-10\text{mW}/^{\circ}\text{C}$ should be applied up to 300mW.

Recommended Operating Conditions

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2.0~5.5	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	dI/dV	0~100 ($V_{CC} = 3.3 \pm 0.3\text{V}$) 0~20 ($V_{CC} = 5 \pm 0.5\text{V}$)	ns/V

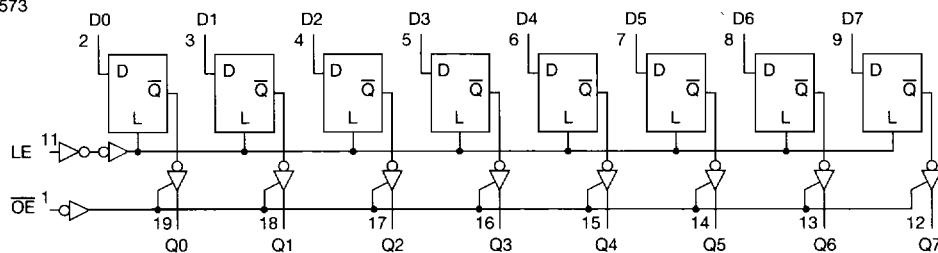
DC Electrical Characteristics

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^{\circ}\text{C}$			$T_a = -40\text{~}85^{\circ}\text{C}$		UNIT
			V_{CC}	Min.	Typ.	Max.	Min.	
High-Level Input Voltage	V_{IH}	—	2.0	1.50	—	—	1.50	V
			3.0	2.10	—	—	2.10	
			5.5	3.85	—	—	3.85	
Low-Level Input Voltage	V_{IL}	—	2.0	—	—	0.50	—	V
			3.0	—	—	0.90	—	
			5.5	—	—	1.65	—	
High-Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -50\mu\text{A}$	2.0	1.9	2.0	—	V
				3.0	2.9	3.0	—	
				4.5	4.4	4.5	—	
			$I_{OH} = -4\text{mA}$	3.0	2.58	—	2.48	
				4.5	3.94	—	3.80	
			$I_{OH} = -24\text{mA}$	5.5	—	—	3.85	
Low-Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 50\mu\text{A}$	2.0	—	0.0	0.1	V
				3.0	—	0.0	0.1	
				4.5	—	0.0	0.1	
			$I_{OL} = 12\text{mA}$	3.0	—	—	0.36	
				4.5	—	—	0.36	
			$I_{OL} = 24\text{mA}$	5.5	—	—	—	
3-State Output Off-State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	2.0	—	—	± 0.5	—	μA
			3.0	—	—	± 0.5	—	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	± 0.1	—	± 1.0
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	8.0	—	80.0

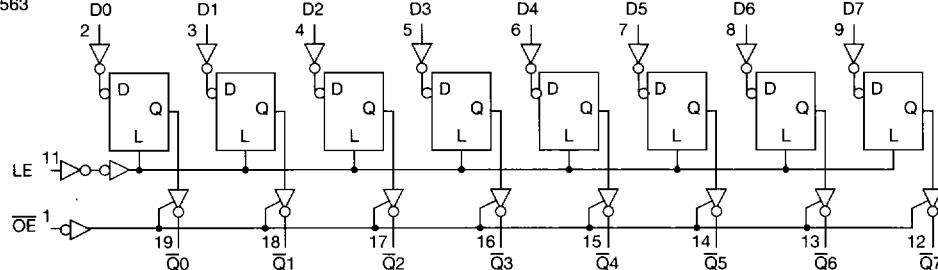
* This spec indicates the capability of driving 50Ω transmission lines.
One output should be tested at a time for a 10ms maximum duration.

System Diagram

TC74AC573



TC74AC563

Timing Requirements (Input $t_r = t_f = 3n$)

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^\circ C$		$T_a = -40-85^\circ C$		UNIT
			V_{CC}	Typ.	Max.	Max.	
Minimum Pulse Width (LE)	$t_{W(H)}$	—	3.3±0.3	—	7.0	7.0	ns
			5.0±0.5	—	5.0	5.0	
Minimum Set-up Time	t_s	—	3.3±0.3	—	7.0	7.0	ns
			5.0±0.5	—	4.0	4.0	
Minimum Hold Time	t_h	—	3.3±0.3	—	1.0	1.0	
			5.0±0.5	—	1.0	1.0	

AC Electrical Characteristics ($C_L = 50\text{pF}$, $R_L = 500\Omega$, Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$T_a = 25^\circ C$			$T_a = -40-85^\circ C$		UNIT	
			V_{CC}	Min.	Typ.	Max.	Min.		
Propagation Delay Time (LE-Q, \bar{Q})	t_{PLH}	—	3.3±0.3	—	9.4	15.4	1.0	17.6	ns
			5.0±0.5	—	6.6	9.9	1.0	11.3	
Propagation Delay Time (Dn-Q, \bar{Q})	t_{PHL}	—	3.3±0.3	—	9.4	16.0	1.0	18.2	
			5.0±0.5	—	6.2	8.9	1.0	10.2	
Output Enable Time	t_{PZL}	—	3.3±0.3	—	9.0	15.2	1.0	17.3	
			5.0±0.5	—	6.3	9.2	1.0	10.5	
Output Disable Time	t_{PZH}	—	3.3±0.3	—	7.0	12.3	1.0	14.0	
			5.0±0.5	—	6.0	8.8	1.0	10.0	
Input Capacitance	C_{IN}	—	—	—	5	10	—	10	pF
Output Capacitance	C_{OUT}	—	—	—	10	—	—	—	
Power Dissipation Capacitance	C_{PD}^1	—	—	—	32	—	—	—	

Note (1): C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation: $I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 8$ (per Latch).

And the total C_{PD} when n pcs. of Latch operate can be gained by the following equation: $C_{PD}(\text{total}) = 21 + 11 \cdot n$.